

Superconducting Quasiparticle-Amplifying Transmons (SQUATs) for THz Photons and meV Phonons

Noah Kurinsky, Hannah Magoon, Jadyn Anczarski, Noshin Tabassum, Chiara Salemi, Caleb Fink, David Schuster RISQ Workshop - 30 May 2024







Phonon Detection



Incident radiation can break Cooper pairs either directly in the superconductor, or indirectly through phonon pathways

Many groups have shown that these radiation events lead to correlated qubit errors:

- McEwen et al., Nature (2021)
- Ristè et al., Nature (2013)
- Serniak et al., Phys. Rev. Letters (2018)
- ✤ Wilen et al, Nature 594, 369 (2021)
- Vepsäläinen et al., Nature (2020)

The effective transmon Hamiltonian parametrized by qubit charging energy E_c and tunneling energy E_I is given by:

 $\widehat{H} = 4E_c (\widehat{n} - n_g)^2 - E_J cos\phi$

Giving us a transition energy of:

 $E_{01} \approx \hbar\omega_0 + \hbar\chi_0 \cos(\pi n_q)$



Superconducting **Qu**asiparticle-**A**mplifying **T**ransmon (SQUAT)









SQUAT Detection Scheme

Materials are chosen such that:

Detection

Readout

$\Delta_{island} \gg \Delta_{junction}$

- 1.) A phonon or photon with energy >2 Δ_{island} breaks a cooper pair into high energy quasiparticles
- 2.) Quasiparticles will downconvert and diffuse. Some energy (~40%) is lost to sub-gap phonons returning to the substrate. Quasiparticles that diffuse into the lower Tc junction region and downconvert further will become trapped



First tests

Efficiency

Island Junction Substrate

SQUAT Detection Scheme

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Detection

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Sensitivity

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3.) Trapped quasiparticles may tunnel back and forth across the junction until recombination. Each tunneling event can be read out as a signal



SQUAT Readout of QP Tunneling Events

Detection

Readout

Efficiency

Sensitivity

First tests

Tunneling events flip the parity state of the qubit, thus changing its transition frequency

- By monitoring the qubit transition frequency, we can count single tunneling events
- SQUAT detector is designed without a readout resonator to reduce pixel size, limit coupling to TLSs, and increase detector efficiency
 - This increases bandwidth relative to Ramsey readout for quantum-limited amplification





SQUAT Projected Efficiency



SQUAT Projected Efficiency



SQUAT Projected Sensitivity



- Measurements of initial devices will help benchmark trapping and tunneling efficiencies
- In devices with small geometric trapping regions, we expect sensitivities in the range of single meV phonons and THz photons



400

300

200

100

Detection Readout Efficiency Sensitivity

First tests





- Aluminum islands
- Aluminum junctions (Manhattan)
- Sapphire substrate
- Fabricated by Jadyn Anczarski and Noshin Tabassum

January 2024 . .

- Aluminum islands
- Aluminum junctions (Dolan)
- Sapphire substrate
- Fabricated by Hannah Magoon with recipe from Ziqian Li

Measurement Setup



Charge Bias Line

First tests

- Weaker coupling to SQUAT (need to drive at higher gains)
- Emitted SQUAT photons are the only thing that are passed to the transmission line for readout



Measurement Setup





CW Measurements

Detection

To track charge offset on the SQUAT island, we can run repeated VNA frequency scans. By fitting the charge dispersion, we can identify correlated events on chip:



Repeated frequency scans display charge jumps over time for two SQUATs on the same chip



Charge dispersion fit values plotted for each qubit

Device Parameters



Readout

Efficiency



First tests

Measurement of two SQUAT devices:

Center Frequency: 7.35 GHz and 8.18 GHz

Quality Factor: 5000-10000

Parity Band Dispersion: 10MHz and 3 MHz

Saturation Pulse Coherence Time: ~300ns



wqubit Saturation Pulse Readout Pulse

Qubit Coupled to Waveguide

Detection Readout Efficiency

Sensitivity

Interesting dynamics emerge as a result of directly reading out the SQUAT's emitted photons

Measurements appear different through the two readout lines as a result of interference with ambient signal photons

We can model this with the Hamiltonian for a two level qubit interacting with a coherent drive field:

First tests

$$H=rac{\omega_q}{2}\sigma_z+rac{\Omega}{2}\left(e^{+i\omega_d t}\sigma_++e^{-i\omega_d t}\sigma_-
ight)$$





Next Steps

Detection Readout Efficiency Sensitivity First tests

Development of low-Tc junctions is of interest for the broader quantum sensing community – whether this is beneficial for quasiparticle cooling is a major question

- Ti junctions made, testing underway
- Hf, AlMn junctions planned
- We will also explore tri-layer processes, but with low-gap materials

Developing readout protocols – likely next devices will have dual feelines to transmit through SQUAT arrays

Question: How low can we get background parity switching rates while maintaining high detection efficiency?





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Backup Slides





SQUAT Dimensions



Nb Gnd Plane Thickness: 100 nm Al Trap Thickness: 200 nm Trap Radius: 112 μm Pixel Diameter: 240 μm Connection Pad Diameter: 4 μm Junction Length: 16 μm Junction Width: 2 μm *(Minimum Junction Width: 0.12 μm)*

SQUAT Sensitivity (varying trapping/tunneling efficiency)



Transmons as Detectors

- McDermott group at UW Madison fabricated an array of 4 weakly charge-sensitive qubits
- By running repeated Ramsey measurements, they were able to track drifts in qubit frequency due to changes in n_g, the island offset charge
- The qubits were found the exhibit spatially correlated jumps in charge due to ambient ionizing radiation
- Furthermore, all qubits on the chip were found to experience degradation in coherence time following radiation events





Wilen et al, Nature 594, 369 (2021) [arXiv:2012.06029]

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Transmons as Detectors

- Plourde group at Syracuse deposited thick electroplated Cu reservoirs on the back of a transmon chip to act as sinks for athermal phonons
- The chips with Cu reservoirs showed reduced ambient tunneling rates compared to identical chips without Cu reservoirs
- The chips with Cu reservoirs showed negligible response to phonon injection events compared to their non-Cu counterparts



Iaia, Ku, Ballard et al, Nature Communications (2022) [arXiv:2203.06586v2]

SQUAT Fabrication Process

First Optical Layer

Detection

Readout

Efficiency

Niobium ground plane and CPW transmission line, made using an optical layer and dry etch

Nb (100 nm)		
Sapphire Wafer		



Nb (100 nm)		
Sapphire Wafer		

Sensitivity

Fabrication

SQUAT Fabrication Process

First Optical Layer

Detection Niobium ground plane and CPW transmission line, made using an optical layer and dry etch

Readout

Efficiency

Sensitivity

Fabrication

Second Optical Layer

Aluminum trap features, made with an optical layer and liftoff

Nb (100 nm) Sapphire Wafer











SQUAT Fabrication Process

First Optical Layer

Detection Niobium ground plane and CPW transmission line, made using an optical layer and dry etch

Readout

Efficiency

Second Optical Layer

Aluminum trap features, made with an optical layer and liftoff

Sensitivity

Fabrication

Ebeam Junction Layer

Aluminum josephson junctions, made with e-beam exposure and liftoff







